



Attorney Docket SEL 154

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of )  
Shunpei YAMAZAKI )  
Serial No.: 09/479,262 )  
Filed: January 5, 2000 )  
Art Unit: 2815 )  
Examiner: E. Wojciechowicz )  
For: Semiconductor Device and )  
Method of Manufacturing )  
the Same )

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231 on October 23, 2001

Signature

Name: Bobbi Wilson

6/A  
1-16-02  
T. Flower

AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

In the Claims:

Please amend claims 1-12, 14-18, and 20-24 to read as follows:

1. (Amended) A semiconductor device comprising:  
a gate electrode formed on an insulting surface;  
a gate insulating film comprising at least a single layer on said gate electrode; and  
a source region, a drain region, and a channel formation region formed between said source region and said drain region, the respective regions begin in contact with said gate insulating film;

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